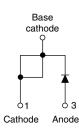
VS-HFA25TB60HN3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 25 A



www.vishay.com



PRODUCT SUMMARY				
Package	TO-220AC			
I _{F(AV)}	25 A			
V _R	600 V			
V _F at I _F	1.7 V			
t _{rr} typ.	23 ns			
T _J max.	150 °C			
Diode variation	Single die			

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA25TB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25TB60 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		600	V	
Maximum continuous forward current	۱ _F	T _C = 100 °C	25		
Single pulse forward current	I _{FSM}		225	A	
Maximum repetitive forward current	I _{FRM}		100		
Maximum namer dissinction	P _D	T _C = 25 °C	125	w	
Maximum power dissipation		T _C = 100 °C	50	vv	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

Revision: 28-Mar-12

Document Number: 94412



RoHS

COMPLIANT

HALOGEN

FREE

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
		I _F = 25 A		-	1.3	1.7	V
Maximum forward voltage	V_{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0	
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7	
Maximum reverse	1	$V_{R} = V_{R}$ rated	See fig. 0	-	1.5	20	
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	600	2000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	55	100	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

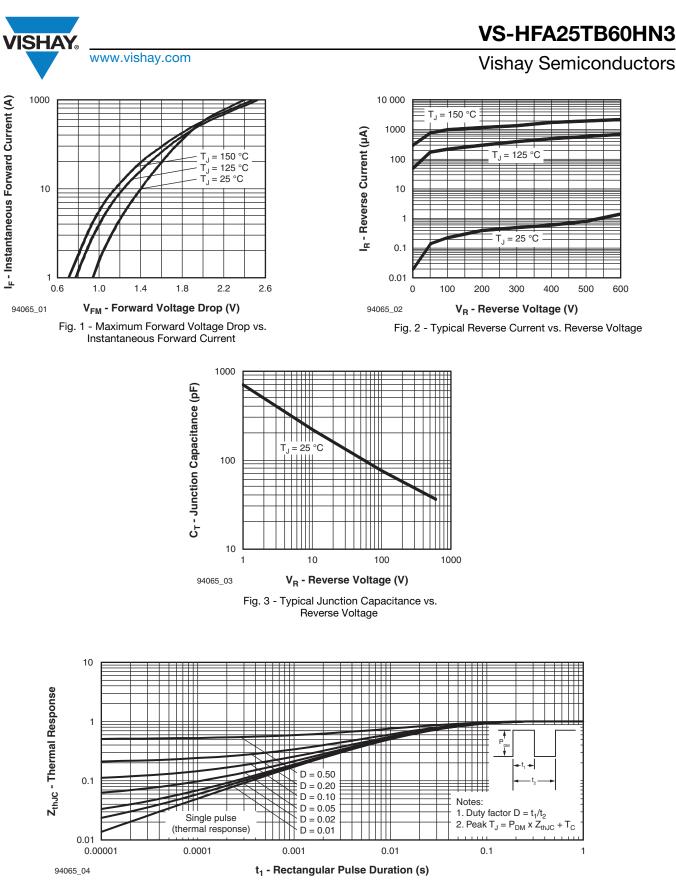
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{V}_R = 30 \text{ V}$		-	23	-	
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C	I _F = 25 A	-	50	75	ns A
t _{rr2}	t _{rr2}	T _J = 125 °C		-	105	160	
Peak recovery current See fig. 7 and 8	I _{RRM1}	T _J = 25 °C		-	4.5	10	
	I _{RRM2}	T _J = 125 °C		-	8.0	15	
Reverse recovery charge	y 200 V		-	112	375		
See fig. 9 and 10		V _R = 200 V	-	420	1200	- nC	
Peak rate of fall of recovery current during t _b See fig. 11 and 12	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-	A/µs
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	γγµs

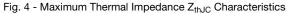
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.0	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AC	HFA25TB60H			

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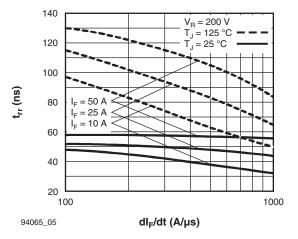


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

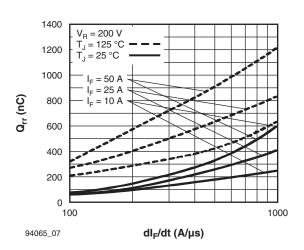


Fig. 7 - Typical Stored Charge vs. dI_F/dt

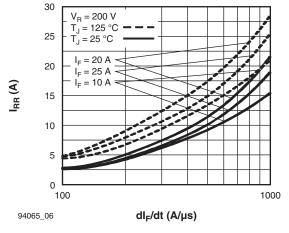


Fig. 6 - Typical Recovery Current vs. dl_F/dt

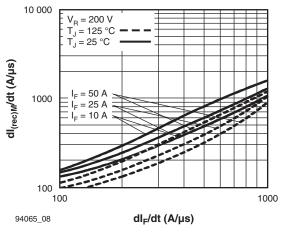


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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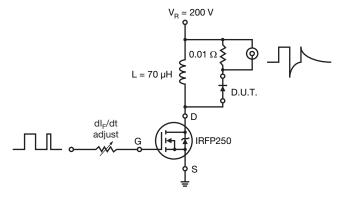


Fig. 9 - Reverse Recovery Parameter Test Circuit

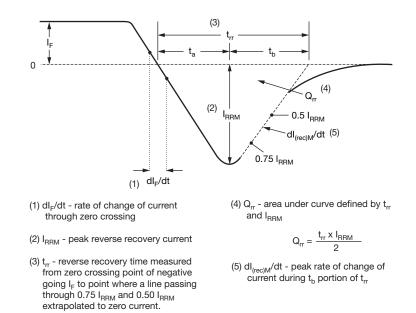


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-HFA25TB60HN3	50	1000	Antistatic plastic tube	

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95221			
Part marking information	www.vishay.com/doc?95068			
SPICE model	www.vishay.com/doc?95471			



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